### 400W, 28V High Power RF LDMOS FETs

#### Description

The MX0540X is a 400-watt, highly rugged, unmatched LDMOS FET, designed for wideband commercial and industrial applications with frequencies HF to 250MHz. It can be used in Class AB/B and Class C for all typical modulation formats.

- •Typical Performance (On Innogration fixture with device soldered):
- $V_{DD}$  = 28 Volts,  $I_{DQ}$  = 2000 mA, CW.

Freq(MHz)	$G_P$ ( dB )	P <sub>-1dB</sub> (W)	Eff(%)	
250	17	380	70	

### Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift

### **Suitable Applications**

- 2-30MHz (HF or Short wave communication)
- 30-88MHz (Ground communication)
- 54-88MHz (TV VHF I)
- 88-108MHz (FM)
- 118 -140MHz (Avionics)

#### Table 1. Maximum Ratings

	-	1				
Rating	Symbol	Value			Unit	
DrainSource Voltage	V <sub>DSS</sub>	+95			Vdc	
GateSource Voltage	V <sub>GS</sub>	-10 to +10		o +10 Vde		
Operating Voltage	V <sub>DD</sub>	+40		Vdc		
Storage Temperature Range	Tstg	-65 to +150		°C		
Case Operating Temperature	Tc			°C		
Operating Junction Temperature	TJ		+225			
Table 2. Thermal Characteristics	·			·		
Characteristic	Symbol	N	Value		it	
Thermal Resistance, Junction to Case	<b>D</b>					
T <sub>C</sub> = 85°C, T <sub>J</sub> =200°C, DC test	Rejc	0.3		°C/W		
Table 3. ESD Protection Characteristics						
Test Methodology		Class				
Human Body Model (per JESD22A114)		Class 2				
Table 4. Electrical Characteristics (T <sub>A</sub> = 25 $^{\circ}$ C ur	nless otherwise noted)					
Characteristic		hal Min	Turn	Мах	Linit	

Characteristic		Symbol	Min	Тур	Max	Unit	

DC Characteristics (per half section)

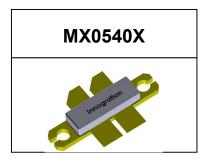


Figure 1. Pin Connection

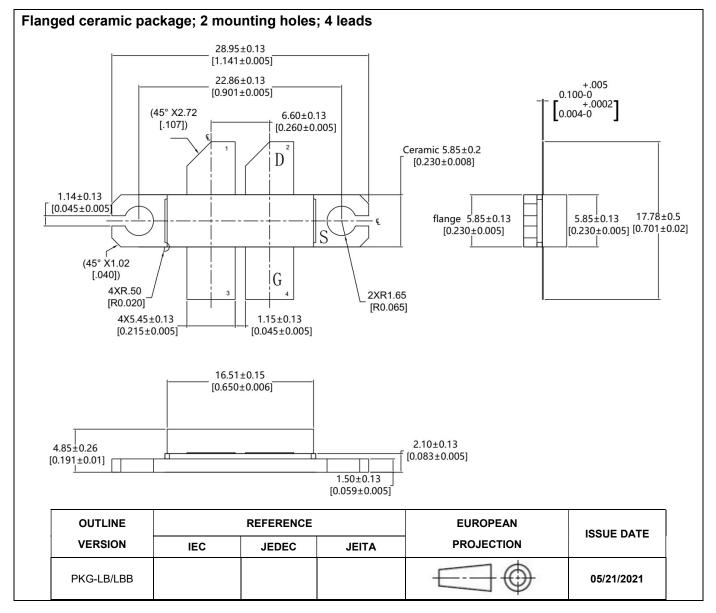
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant
- 136-174MHz (Commercial ground communication)
- 160-230MHz (TV VHF III)

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Drain-Source Voltage	V <sub>(BR)DSS</sub> 95		98		v	
V <sub>GS</sub> =0, I <sub>DS</sub> =1.0mA	V (BR)DSS	90	50		v	
Zero Gate Voltage Drain Leakage Current				1	μA	
(V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0 V)	I <sub>DSS</sub>					
Zero Gate Voltage Drain Leakage Current				1	μA	
(V <sub>DS</sub> = 28 V, V <sub>GS</sub> = 0 V)	I <sub>DSS</sub>					
GateSource Leakage Current				1	μΑ	
(V <sub>GS</sub> = 10, V <sub>DS</sub> = 0 V)	I <sub>GSS</sub>					
Gate Threshold Voltage			2.19		V	
(V <sub>DS</sub> = 28V, I <sub>D</sub> = 650 μA)	V <sub>GS</sub> (th)				v	
Gate Quiescent Voltage			3.0		V	
( $V_{DD}$ = 28 V, $I_D$ = 1.0 A, Measured in Functional Test)	$V_{GS(Q)}$					
Common Source Input Capacitance			187		»Г	
(V <sub>GS</sub> = 0V, V <sub>DS</sub> =28 V, f = 1 MHz)	C <sub>ISS</sub>		107		pF	
Common Source Output Capacitance	C <sub>oss</sub>		79		pE	
(V <sub>GS</sub> = 0V, V <sub>DS</sub> =28 V, f = 1 MHz)	Coss		19		pF	
Common Source Feedback Capacitance	6		4.6		- 5	
(V <sub>GS</sub> = 0V, V <sub>DS</sub> =28 V, f = 1 MHz)	C <sub>RSS</sub>		4.0		pF	
unctional Tests (In Demo Test Fixture, 50 ohm system) $V_{DD}$ = 28 V	′dc, I <sub>DQ</sub> = 2000 mA	, f =250 MHz,	CW Signal Me	asurements.		
Power Gain	Gp		17		dB	
Drain Efficiency@P1dB	ηD		70		%	
1 dB Compression Point	P <sub>-1dB</sub>		380		W	
Input Return Loss	IRL		-7		dB	

VSWR 20:1 at 380W pulse CW Output Power	No Device Degradation
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### **Package Outline**



### **Revision history**

#### Table 5. Document revision history

Date	Revision	Datasheet Status
2018/03/13	Rev 1.0	Product Datasheet
2019/10/16	Rev 1.1	Modified to rugged version with X suffix ,modified upper frequency
2022/9/19	Rev 1.2	LBB Pkg outline updated

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